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| FORM PTO-1449 (Rev. 7-80) Trademark Office | U.S. Dept. of Commerce Patent and | Atty. Docket No. 422.04 | Appl. No. 10/052,049 |
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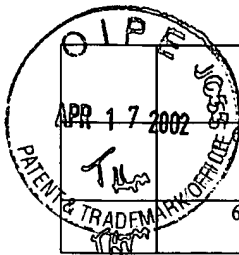
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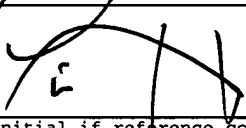
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